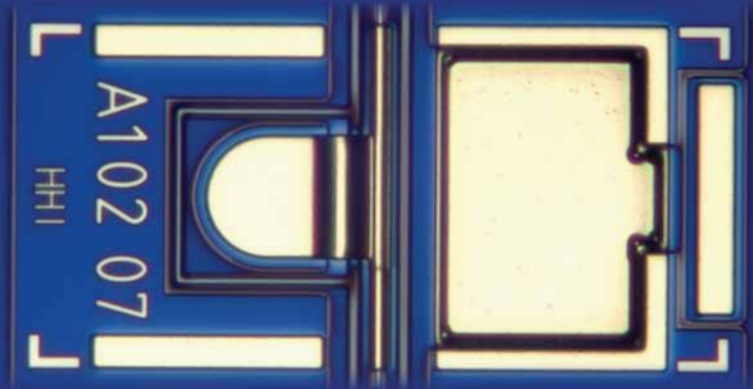


Laser Technology



Types and structures:

- InGaAsP/InGaAsP-MQW and InGaAlAs/InGaAlAs-MQW
- RW, BH, and BA laser structures
- FP, DFB, DBR, multisection, EMLs, gain elements, monolithically integrated
- Flip-chip mountable (surface-n-contact)
- Integrated heater for wavelength tuning
- Electron beam defined DFB gratings
- Integrated beam forming (taper)

Laser Diodes and LEDs

- Wavelength range 1.2 - 1.9 μm
- Output power up to 700mW cw (BH, RW)
- Output power up to 18W pulse (BA)
- Modulation up to 25GHz (RW)
- Modulation up to 70GHz (EML)
- Uncooled operation

Our Services:

- Consulting and feasibility studies
- Development of components according to customer specifications, from simulation to prototypes ('tailored' wavelengths)
- Full or partial processing of laser diodes
- Low to medium volume production on own InP semiconductor processing line
- Cooperation with industrial partners for volume production

For more detailed information, references and offers please contact us

CONTACT

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